RICOH

Li-ion / Li-polymer Battery Management Analog Front-End IC

OVERVIEW

The R5602 is an analog front-end IC for 4-cell to 7-cell Li-ion / Li-polymer battery management. This IC provides cell voltage monitor, bidirectional current monitor based-on monitoring the voltage across an external sense resistor, two input pin for temperature monitoring by external NTC thermistors, Die temperature monitor, overcurrent protection, high-side NMOSFET control, a voltage regulator, cell balancing switches, switch for open-wire detection and I²C/SPI interface. The IC has a built-in A/D converter and an MCU can read each monitor value as a digital value.

KEY BENEFITS

- High accuracy voltage monitoring and low power consumption for saving battery life.
- Control High-side NMOSFET for ease of treatment and cost reduction of BOM.
- No limitation in cell connection sequence for cost reduction of battery pack assembling.

KEY SPECIFICATIONS

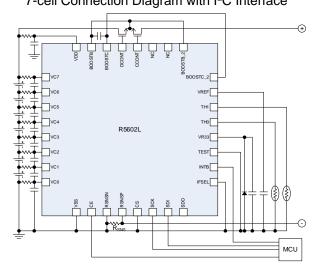
- Absolute Maximum Rating: 40 V
- Power Consumption Active: Typ. 150 μA Standby: Max. 1.0 μA
- Built-in 12-bit A/D Converter
- Cell Voltage Monitor:
 - Input Range: 1.5 V to 4.5 V Accuracy: +/-30mV⁽¹⁾
- Current monitor based-on monitoring voltage across sense resistor
 - Gain: x2.5, x10, x20
- Temperature monitoring by two external NTC thermistors
- Die temperature monitoring and high temperature alert.
- Monitoring Speed: less than 1ms/1monitor (Max)
- Overcurrent Protection by Detectors: Overcharge, overdischarge, and short-circuit
- Voltage Regulator Output: Typ.3.4 V
- High-side NMOSFET Control
- Built-in Cell Balancing Switch: Cell Balancing Current depends on external resistor (up to 20mA)
- Built-in switch for Open-wire detection
- No limitation in cell connection sequence when CE = Low
- I²C / SPI interface with/without CRC

APPLICATIONS

7-cell Connection Diagram with I²C Interface

TYPICAL APPLICATION

No.EA-531-210401



 PACKAG
 QFN0505-32C

 5mm x 5mm x 0.8mm

Power Tool, Power Storage, Cordless/Robot Cleaner, Pedelec, E-bike, Drone

⁽¹⁾ $-20^{\circ}C \le Ta \le 85^{\circ}C$, $V_{VCIN} = 3 V$ to 4.2 V, $V_{DD} \ge 6.0 V$. Cell voltages are balanced.

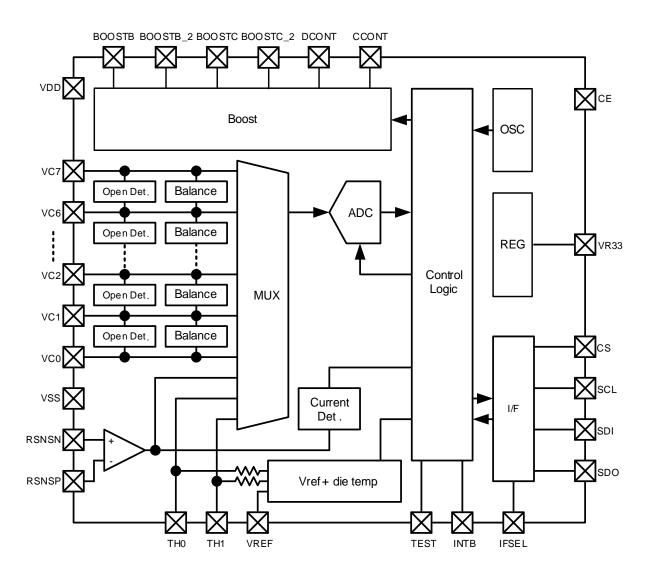
No.EA-531-210401

SELECTION GUIDE

Selection Guide

Product Name	Product Name Package		Pb Free	Halogen Free		
R5602L001AA-E2	QFN0505-32C	5,000 pcs	Yes	Yes		

BLOCK DIAGRAM

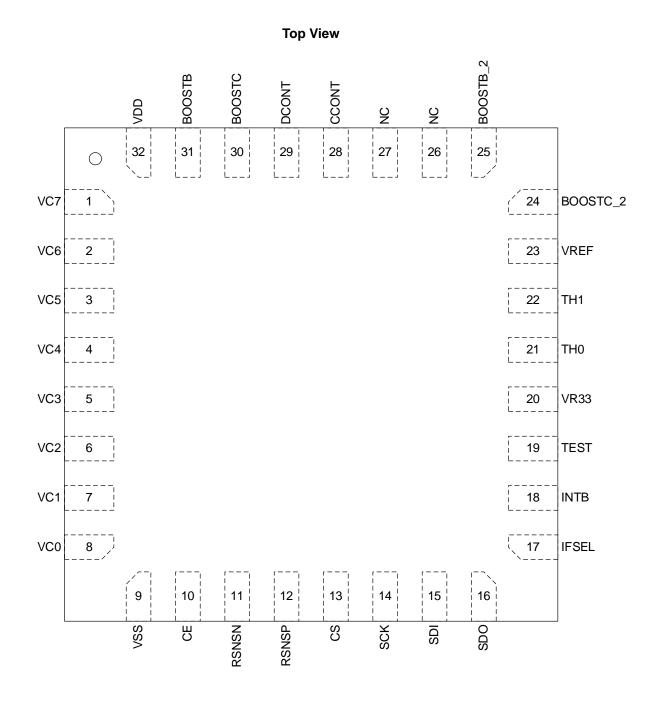


R5602L Block Diagram

RICOH

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PIN DESCRIPTION



R5602L (QFN0505-32C) Pin Configuration

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R5602L Pin	Description
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Pin No.	Pin Name	I/O	D/A	Description
1	VC7	Ι	A/P/G	Positive Pin for Cell 7
2	VC6	Ι	A/P/G	Positive Pin for Cell 6
3	VC5	Ι	A/P/G	Positive Pin for Cell 5
4	VC4	Ι	A/P/G	Positive Pin for Cell 4
5	VC3	Ι	A/P/G	Positive Pin for Cell 3
6	VC2	Ι	A/P/G	Positive Pin for Cell 2
7	VC1	Ι	A/P/G	Positive Pin for Cell 1
8	VC0	Ι	A/P/G	Negative Pin for Cell 1
9	VSS	-	G	Ground Pin
10	CE	-	D	Chip Enable Pin
11	RSNSN	-	А	R _{SENS} Negative Input Pin
12	RSNSP	-	А	R _{SENS} Positive Input Pin
13	CS	-	D	SPI Chip Select Pin
14	SCK	Ι	D	Clock Input Pin in Common to SPI and I ² C
15	SDI	Ю	D	Input Pin for SPI Data, Input / Output Pin for I ² C Data
16	SDO	0	D	Output Pin for SPI Data
17	IFSEL	Ι	D	SPI / I ² C Switching Pin (High: SPI, Low: I ² C)
18	INTB	0	D	Interrupt Output Pin (Nch Open-drain Output)
19	TEST	Ι	D	Connect to GND
20	VR33	0	А	Capacitor and Clamp Diode Connecting Pin for Power Supply
21	TH0	-	А	Thermistor Connecting Pin 0
22	TH1	Ι	Α	Thermistor Connecting Pin 1
23	VREF	0	А	Reference Voltage Capacitor Pin for Internal Use Only
24	BOOSTC_2	-	А	Boost Voltage Input Pin
25	BOOSTB_2	Ι	Α	Boost Reference Voltage Input Pin
26	NC	-	-	Non-Connection
27	NC	-	-	Non-Connection
28	CCONT	0	Α	FET Control Pin for Charger, High Potential SPI Chile Select Pin
29	DCONT	0	Α	FET Control Pin for Discharger
30	BOOSTC	0	Α	Boost Voltage Pin
31	BOOSTB	-	Р	Boost Reference Voltage Pin
32	VDD	-	Р	Power Supply Pin

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ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Pin	Rating	Unit
Power Supp	ly Voltage			•
N/			- 0.3 to 40	V
V _{PS1}	Power Supply Voltage1	VDD	V _{IN1_6} - 0.3 to V _{IN1_6} + 6	V
V _{PS2}	Power Supply Voltage2	BOOSTB	- 0.3 to 40	V
Input Voltage	e Range			
V _{IN1_n}	Input Voltage Range 1	VCn	$V_{IN1_{(n-1)}}$ - 0.3 to $V_{IN1_{(n-1)}}$ + 6.0	V
V _{IN2}	Input Voltage Range 2	VC0	V_{SS} – 0.3 to V_{SS} + 0.3	V
VIN3	Input Voltage Range 3	RSENSN, RSNSP	Vss - 0.3 to Vout1 + 0.3	V
V _{IN4}	Input Voltage Range 4	TH0, TH1	Vss - 0.3 to Vout1 + 0.3	V
V _{IN5}	Input Voltage Range 5	CE	V _{SS} – 0.3 to 6.0	V
V _{IN6}	Input Voltage Range 6	CS, TEST, IFSEL	Vss - 0.3 to Vout1 + 0.3	V
M		SDI, SCK(SPI)	V _{SS} – 0.3 to V _{OUT1} + 0.3	V
Vin7	Input Voltage Range 7	SDI(I/O), SCK(I ² C)	V _{SS} – 0.3 to 6.0	V
V _{IN8}	Input Voltage Range 8	BOOSTB_2	VPS2	V
V _{IN9}	Input Voltage Range 9	BOOSTC_2	V _{OUT5}	V
Output Volta	ige Range			
Vout1	Output Voltage Range 1	VR33	V _{SS} – 0.3 to 6.0	V
V_{OUT2}	Output Voltage Range 2	VREF	V_{SS} – 0.3 to V_{OUT1} + 0.3	V
Vout3	Output Voltage Range 3	INTB	V _{SS} – 0.3 to 6.0	V
Vout4	Output Voltage Range 4	SDO	Vss - 0.3 to Vout1 + 0.3	V
V_{OUT5}	Output Voltage Range 5	BOOSTC	V_{PS2} – 0.3 to V_{PS2} + 6	V
Vout6	Output Voltage Range 6	CCONT, DCONT	V _{PS2} - 0.3 to V _{OUT5} + 0.3	V
ESD	-			_
CDM	Charged Device Model		± 0.5	kV
Power Dissi	pation			
PD	Power Dissipation	Refer to A	Appendix "Power Dissipation".	
Temperature	Range		1	
Tj	Junction Temperature Range		- 40 to 125	°C
Tstg	Storage Temperature Range		- 55 to 125	°C

(n: 1 to 7)

ABSOLUTE MAXIMUM RATINGS

Electronic and mechanical stress momentarily exceeded absolute maximum ratings may cause permanent damage and may degrade the lifetime and safety for both device and system using the device in the field. The functional operation at or over these absolute maximum ratings is not assured.

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RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Rating	Unit	
V _{DD}	Power Supply Voltage	6.0 to 31.5	V	
V _{BSTB}	Boost Reference Supply Voltage	0 to V _{DD}	V	
VVCIN	Cell Voltage Input Range (Vcn –Vcn-1)	1.5 to 4.5	V	
V _{C0}	Negative Pin for Cell 1 Voltage	0	V	
Vrsnsn	RSENS Negative Input Pin Voltage	0	V	
	Derve Desitive Input Din Veltage	-0.35 / [IS_GAIN] ⁽¹⁾	V	
Vrsnsp	RSENS Positive Input Pin Voltage	to 1.65 / [IS_GAIN]	V	
VTHERM	TH0 and TH1 Input Pin Voltage	0.25 to 2.25	V	
Та	Operating Temperature Range	-20 to 85	°C	

Recommended Operating Conditions

(n: 1 to 7)

RECOMMENDED OPERATING CONDITIONS

All of electronic equipment should be designed that the mounted semiconductor devices operate within the recommended operating conditions. The semiconductor devices cannot operate normally over the recommended operating conditions, even if they are used over such conditions by momentary electronic noise or surge. And the semiconductor devices may receive serious damage when they continue to operate over the recommended operating conditions.

⁽¹⁾ [IS_GAIN] is set to 2.5, 10, or 20 by register.

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ELECTRICAL CHARACTERISTICS

	acteristics		T		```	25°C)
Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
Cell Bal	ancing					_
I _{CBn}	Cell Balancing Current	$V_{Cn} - V_{C(n-1)} = 4.0 V$ 100 Ω input-resistor			20	mA
I _{LVCn} ⁽¹⁾	Input leakage Current of middle Cell	$V_{Cn} - V_{C(n-1)} = 4.5$ V, CE: High, Cell Balancing: OFF, Cell Voltage Monitor: OFF			0.5	μA
Cell Vol	age Monitor (A/D Convert	er: ADC)				
VVCIN	Cell Voltage Input Range	V _{Cn} - V _{C(n-1)}	1.5		4.5	V
		Ta = 25° C, V _{VCIN} = 4.0 V, Cell voltages are balanced.	-15		15	mV
	Monitoring Accuracy for Cell Voltage	-20° C ≤ Ta ≤ 85°C, 1.5 V ≤ V _{VCIN} < 2.5 V, Cell voltages are balanced.	-40		40	mV
Vvca		$-20^{\circ}C \le Ta \le 85^{\circ}C$, 2.5 V $\le V_{VCIN} < 3$ V, Cell voltages are balanced.	-35		35	mV
		-20° C ≤ Ta ≤ 85°C, 3 V ≤ V _{VCIN} ≤ 4.2 V, Cell voltages are balanced.	-30		30	mV
		-20° C ≤ Ta ≤ 85°C, 4.2V < V _{VCIN} ≤ 4.5 V, Cell voltages are balanced.	-35		35	mV
Input Cu	Irrent Monitoring (ADC)	· · · · ·				
	Monitoring Ranges for	$R_{SNS} = 5m\Omega$, [IS_GAIN] = 20	-3.5		16.5	Α
ICUR	Input Current	$R_{SNS} = 1m\Omega$, [IS_GAIN] = 2.5	-140		660	Α
		$R_{SNS} = 5m\Omega$, [IS_GAIN] = 20	-1		1	Α
ICUA	Monitoring Accuracy for	$R_{SNS} = 5m\Omega$, [IS_GAIN] = 10	-1.4		1.4	Α
	Input Current	$R_{SNS} = 5m\Omega$, [IS_GAIN] = 2.5	-2.4		2.4	A

(n: 1 to 7)

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DC Chara	acteristics (Continued)				(Ta	= 25°C)
Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
Current	Protection					
Rsns	Resistance Range for SENSE Pin		1		5	mΩ
I _{SHORT}	Setting of Short-circuit Current ⁽¹⁾	$[S_{SHORT}] = 2.4, R_{SNS} = 5m\Omega$ $[IS_GAIN] = 20$		18		А
Icuas	Short-circuit Current Detection Accuracy		-10		+10	%
IDOC	Setting of Discharge Overcurrent ⁽²⁾	$[S_{DOC}] = 1.4, R_{SNS} = 5m\Omega$ $[IS_GAIN] = 20$		8		А
I _{CUAD}	Discharge Overcurrent Detection Accuracy		-20		+20	%
lcoc	Setting of Charge Overcurrent ⁽³⁾	[S _{COC}] = 0.05, R _{SNS} = 5mΩ [IS_GAIN] = 20		-5.5		А
Icuac	Charge Overcurrent Detection Accuracy		-25		+25	%
Voltage I	Regulator					
V _{VR33}	Output Voltage	-20°C ≤ Ta ≤ 85°C, V _{DD} ≥ 6.0V I _{OUT} ≤ 10mA	3.2	3.4	3.5	V
ILIM	Output Current Limit		10			mA
Die Tem	perature Detection					
	Abnormal Detection Temperature at Die High- temperature			150		°C
T _{SDR}	Abnormal Release Temperature at Die High- temperature			125		°C
NTC (Ne	gative Temperature Coeffi	cient) Thermistor for Monitoring	•			
R_{THn}	NTC Pulled-up Resistance			10		kΩ
Boost Vo	oltage for BOOSTC Pin					
V _{BSTC}	Voltage Boost		V _{вsтв} +4.3	V _{вsтв} +5		V
FET Con	troller for DCONT, CCONT	Pin				
VFETH	FET (DCONT, CCONT) Pin Output Voltage, High	lоuт = 0		VBSTC		V
VFETL	FET (DCONT, CCONT) Pin Output Voltage, Low	lоuт = 0		VBSTB		V
I _{FETIL}	FET (DCONT, CCONT) Pin Output Current, Low	$V_{FET} = V_{BSTC} = V_{BSTB} + 6V,$		2		mA

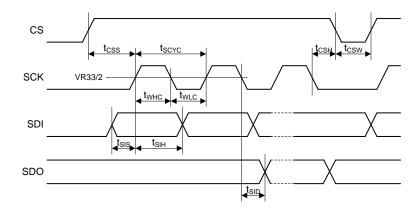
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Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
Input V	oltage for CS / CE / IFSEL Pin				1	
Vcsh	CS Pin Input Voltage, High		V _{VR33} ×0.8			V
Vcsl	CS Pin Input Voltage, Low				V _{VR33} ×0.2	V
VIFSEL	IFSEL Pin Input Voltage, High		V _{VR33} ×0.8			V
VIFSEL	IFSEL Pin Input Voltage, Low				V _{VR33} ×0.2	V
V_{CEH}	CE Pin Input Voltage, High		3.0		5.5	V
VCEL	CE Pin Input Voltage, Low		-0.3		0.3	V
Output	Voltage for INTB Pin (Nch Open	-drain Output)				
Vintel	INTB Pin Output Voltage, Low	$I_{OL} = 3 \text{ mA}$			0.4	V
Current	Consumption	•	·			
Icc	Current Consumption	Active ⁽¹⁾		150	300	μA
		Standby			1.0	μA
Serial Ir	nterface					
SCK: C	MOS Input Pin (Schmitt Input)					
VIH	Input Voltage, High		V _{VR33} ×0.7			V
VIL	Input Voltage, Low				V _{VR33} ×0.3	V
V _{HIS}	Schmitt Hysteresis Voltage		V _{VR33} ×0.05			V
SDI: CN	IOS Input Pin (Schmitt Input / N	ch Open-drain Outpu	t)			
VIH	Input Voltage, High		V _{VR33} ×0.7			V
VIL	Input Voltage, Low				V _{VR33} ×0.3	V
V _{HIS}	Schmitt Hysteresis Voltage		V _{VR33} ×0.05			V
Vol	Output Voltage, Low	lo∟ = 3 mA			0.4	V
SDO: C	MOS Output Pin				1	
Voh	Output Voltage, High	I _{OH} = -3 mA	V _{VR33} - 0.4			V
• 011						

 $[\]underline{^{(1)}$ 7-cell (Vc_TIME = 80µs) every 2ms. Alert and FET control OFF.

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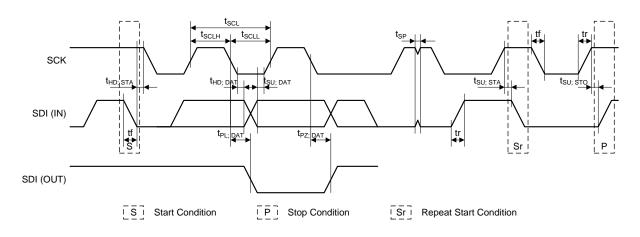
AC Chai	racteristics				(Ta =	25°C)
Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
Single/S	Sequential Read and Detection	Delay Time	·			
t _{AC}	Time Accuracy		-20		30	%
SPI Con	nmunication		·			
tscyc	SCK Clock Cycle Time		1			μs
twнc	SCK Clock Cycle Time, High		400			ns
t _{WLC}	SCK Clock Cycle Time, Low		400			ns
tsis	Serial Data Set-up Time		100			ns
tsıн	Serial Data Hold Time		100			ns
t _{csw}	Setup Time for Transmission and Reception		3			μs
tcss	Setup Time for Chip Enable		200			ns
tсsн	Hold Time for Chip Enable		200			ns
t _{SID}	Delay Time for Serial Data				200	ns



SPI Bus Timing Diagram

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AC Char	acteristics (Continued)				(Ta	= 25°C)
Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
I ² C Com	munication		·			
fськ	SCK Clock Frequency				400	kHz
tsc∟	SCK Clock Cycle		2.5			μs
tscll	SCK Clock, Low		1.3			μs
t sclh	SCK Clock, High		0.6			μs
t _{su:sta}	Start Condition Setup Time		0.6			μs
tsu:dat	Data Setup Time		200			ns
tsu:sto	Stop Condition Setup Time		0.6			μs
t _{HD:STA}	Start Condition Hold Time		0.6			μs
thd:dat	Data Hold Time		0			ns
tr	Rising Time for SDI and SCK				300	ns
t _f	Falling Time for SDI and SCK				300	ns
tpl:dat	Falling Time required for SDI output Low	After falling of SCK			0.9	μs
t pz:dat	Rising Time required for SDI output High	After falling of SCK			0.9	μs
t _{SP}	Removal Spike Width by Input Filters				50	ns
Св	Capacitive Load for SDI and SCK Bus lines				50	pF



I²C Bus Timing Diagram

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THEORY OF OPERATION

Internal 12-bit ADC

The R5602L has a 12-bit high-accuracy analog-digital converter (ADC), and it can measure cell voltages for the VCn pins, the voltage between the RSNSP and the RSNSN pins generated by charge/discharge current, a voltage divided by an external NTC and an internal resistor, and an internal voltage to monitor the die temperature. While measuring one voltage, the R5602L is impossible to measure another voltage.

Cell Voltage Monitoring

After the analog-to-digital converting by order of the micro-controller unit (MCU), the data for cell voltages $V_{Cn} - V_{C(n-1)}$ (n: 1 to 7) is stored into the internal registers. The MCU can read each cell voltage from the register.

Current Monitoring

The R5602L can read a current that flows via the RSENS resistor between the RSNSN and the RSNSP pins. By following the MCU, the R5602L measures the difference voltage between the RSNSN pin and the RSNSP pin to multiply it by a gain and stores it into the internal register.

The MCU can read the measured voltage from the internal register with the three-step selectable gain of 2.5 / 10 / 20 times.

Temperature Monitoring

[Outside]

By connecting a 10 k Ω NTC thermistor between VSS and TH0 / TH1 pin, the R5602L can supervise the temperatures for external two points of the device. The TH0 and the TH1 pins are pulled-up to the reference voltage 2.5 V with 10 k Ω resistor connected internally to each pin.

[Inside]

By following the MCU's supervising order, the R5602L can measure the voltage met the temperature sensed in the internal temperature-monitoring circuit. The MCU can read the voltage from the register. When the internal temperature is high, an alert signal can be output via the INTB pin.

Sequential Read

The R5602L can monitor the following data of items in sequence.

- 1. VC7 \rightarrow VC6 \rightarrow VC5 \rightarrow VC4 \rightarrow VC3 \rightarrow VC2 \rightarrow VC1
- 2. Current via Charger / Discharger path
- 3. Die Temperature
- 4. TH1 Temperature
- 5. Th0 Temperature

When using six-cell or less, the connected cell only can be selected to monitor its voltage. The MCU can control above items of 2 to 5 regardless of the cell voltage.

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Overcurrent Detection

Overcurrent Detection is a function to detect overcurrent by the current monitoring. After detection, this function is reset by the external MCU. The overcurrent detection voltage and the overcurrent detection delay time are settable for each of charge and discharge.

High-side NMOSFET Control

By following the MCU's order, the R5602L can control outputs of the CCONT and the DCONT pins that control High-side NMOSFETs. Outputs of the CCONT and the DCONT pins become a CMOS output with the BOOSTC voltage that was risen up as reference to the BOOSTB voltage. Setting the pin to Low can turn off the FET, setting it to High can turn on the FET. When the MCU enable current protection, the CCONT pin becomes Low if detected charge overcurrent, the DCONT pin becomes Low if detected discharge overcurrent or detected short. When the MCU disable current protection, the MCU should turn NMOSFET off at the overcurrent.

Cell Balancing

When the MCU controls the cell balancing switch, the R5602L can flow the discharge current for each cell into the IC. The discharge current value is set with the external resistor. Select external components with due consideration for the power dissipation of the device and external components.

Open-wire Detection

By flowing the discharge current for each cell into the internal resistor of the device, the R5602L monitors the cell voltage and the MCU can detect an open-wire.

INTB Pin Output

When the R5602L detects an event such as the followings, the INTB pin outputs Low. As the output type of the INTB pin is NMOSFET open-drain, pull up it with external resistors.

- Abnormal detection at die high-temperature
- Completion of start-up
- Low-voltage detection VR33 pin output
- CRC error detection
- Completion of ADC read
- Discharge overcurrent detection
- Charge overcurrent detection
- Short-circuit detection

Standby Mode

When the CE pin is Low, the R5602L is in the Standby state and registers become initial settings. Usually, setting the CE pin to High goes to the Normal state.

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Serial Communication Interfaces

As for communication method to the MCU, the R5602L can select either of two kinds of serial interfaces, SPI or I²C.

Method	Control Pin	Pin Name
	CS (Chip Select)	CS
SPI	SCK (Serial Clock)	SCK
(IFSEL: High)	MISO (Master In Slave Out)	SDO
	MOSI (Master Out Slave In)	SDI
l ² C	SCL (Serial Clock)	SCK
(IFSEL: Low)	SDA (Serial Data)	SDI

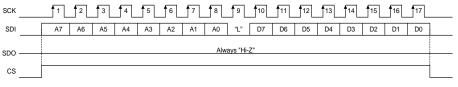
When using the I^2C interface, set the CS pin to VSS.

SPI Communication

Setting the IFSEL pin to High enables the communication with the SPI interface. This interface has four pins of serial clock (SCK), serial data input pin (SDI), serial data output pin (SDO), and chip-select input pin (CS). The following Write / Read processing is shown as viewed from the master. On the data transferring, Master must transfer from the most significant bit (MSB) of the byte data, first. Likewise, on the data receiving, Slave (R5602L) must transfer from MSB of the byte data first.

[Write Processing]

- 1. The data is loaded into the internal shift-register at rising edge of SCK (SCK Frequency: Max.1MHz).
- 2. During the CS pin of High, the data receiving becomes enabled (Active-High). However, the write processing does not work if fixing to High.
- 3. The loaded data is transferred from the SDI pin, in order of 8-bit address data, one bit for Low data, and 8-bit control command data in the control register.



Write Timing (No CRC)

No.EA-531-210401

4. Setting the CRC_EN register to "1" enables to transfer the data including CRC data (Initial value of [CRC_EN] is "0"). In the case of the data including CRC, 8-bit packet error code (PEC) is transferred after the above transferring. The CRC is calculated over the 8-bit address data, one bit for Low data, and 8-bit control command data. The CRC data is given by the following polynomial.

 $C(x) = X^8 + X^2 + X^1 + 1$

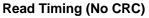
SCK	1	2	3	4	5	6	7	8	9	10	11	12	13	14	15	16	17	18	19	20	21	22	23	24	25	
SDI	A7	A6	A5	A4	A3	A2	A1	A0	"L"	D7	D6	D5	D4	D3	D2	D1	D0	C7	C6	C5	C4	C3	C2	C1	C0]
SDO —	Always "Hi-Z"																									
CS																										

Write Timing (Including CRC)

[Read Processing]

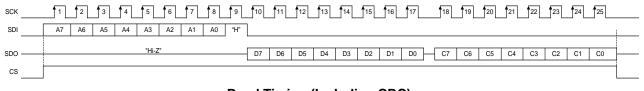
- 1. The data is loaded into the internal shift-register at rising edge of SCK (SCK Frequency: Max.1MHz).
- 2. During the CS pin of High, the data receiving and transferring becomes enabled (Active-High). However, the read processing does not work if fixing to High.
- 3. After 8-bit address data and one bit for High data is transferred from the SDI pin, 8-bit control register specified is transferred from the SDO pin.

SCK	1	2	1 3	4	5	6	7	8	9	10	11	12	13	14	15	16	17	
SDI	A7	A6	A5	A4	A3	A2	A1	A0	"H"									
SDO					"Hi-Z	-				D7	D6	D5	D4	D3	D2	D1	D0	<u> </u>
cs																		1



4. Setting the CRC_EN register to "1" enables to transfer the data including CRC data (Initial value of [CRC_EN] is "0"). In the case of the data including CRC, 8-bit packet error code (PEC) is transferred after the above transferring. The CRC is calculated over the 8-bit address data, one bit for High data, and 8-bit read data. The CRC data is given by the following polynomial.

```
C(x) = X^8 + X^2 + X^1 + 1
```



Read Timing (Including CRC)

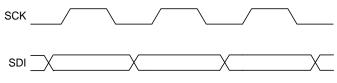
No.EA-531-210401

■ I²C Interface Communication

Setting the IFSEL pin to Low enables the communication with the I²C interface. Each of the SCK and the SDI pins equates to the SCL and the SDA pins in the SPI interface.

Availability of Data

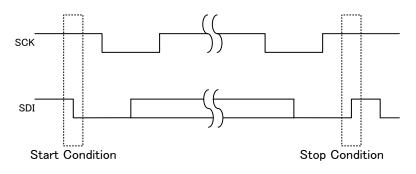
During the SCK pin of High for the data transferring duration, the SDI data of I²C-bus must be maintained constant. The SDI can change between High and Low states only when the SCK pin is Low except Start and Stop conditions.



SDI Timing Chart

Start and Stop Conditions

The SCK and the SDI pins are pulled up to High except for the data transferring duration. The start condition is met when being pulled the SDI pin down from High to Low, and the start and the stop conditions are generated by master only.



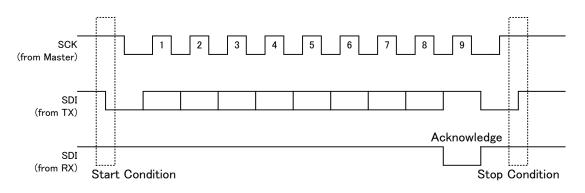
Start and Stop Conditions

Data Transfer Method

After the start condition is generated, the data transferring is done every one-byte from the MSB of a byte. An acknowledge signal is sent from the receiver to the sender at the end of transferring one-byte data.

After transferring a byte data, the master as sender makes the SDI signal Open (= High) and the slave (R5602L) makes the SDI signal Low as acknowledge signal. On the other hand, the slave as sender makes the SDI signal Open (= High). If maintaining to receive the acknowledge signal without interruption, the master makes the SDI signal Low. The master can indicate the end of the data transferring to the slave by making the SDI signal Open (= High).

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Data Transfer when Master is Sender

Format for Data Transfer

The format to transfer data via the I²C bus is as follows. Be sure to begin with start condition and finish with stop condition. On the data transferring, Master must transfer from the most significant bit (MSB) of the byte data, first. Likewise, on the data receiving, Slave (R5602L) must transfer from MSB of the byte data first.

[Write Processing]

The format for write processing after the start condition consists as shown in the following figure.

1st byte: Slave address (32h = 0110010b) + Write instruction

2nd byte: Address for internal register to write the data.

3rd byte: Data to write in the second byte.

4th byte: Packet error code (PEC) if including the Cyclic Redundancy Check (CRC) data.

The PEC is an 8-bit data to indicate the result of the CRC error detection. The CRC data is given by the following polynomial.

$C(x) = X^8 + X^2 + X^1 + 1$

The CRC is calculated for the slave address, register address, and data. When burst write transaction, the CRC for subsequent data bytes is calculated for the data byte only.

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Slave Address (7bit) Address "n" (8bit) ACK Star SA6 SA5 SA4 SA3 SA2 SA1 SA0 R/WB ACK A7 A6 A5 A4 A3 A2 A1 A0 SCK SDI 0x32 Data of Address "n" (8bit) PEC "n" (8bit) D4 D3 D2 C4 C3 ACK D5 D1 ACK C7 C6 C5 C2 C1 C0 PEC "n+1" (8bit) Data of Address "n+1" (8bit) D5 D4 D3 D2 D0 ACK C7 C6 C5 C4 C3 C1 C0 ACK D7 D6 D1 C2 Data of Address "n+x" (8bit) PEC "n+x" (8bit) D6 D5 D4 D3 D2 D1 D0 ACK C7 C6 C5 C4 C3 C2 C1 C0 ACK Stop D7 : Output from Master

An example of the burst write format is as follows:

Write Timing Chart (with CRC, Continuous writing)

[Read Processing]

The format for read processing after the start condition consists as shown in the following figure.

1st byte: Slave address (32h = 0110010b) + Write instruction

 2^{nd} byte: Address for the internal register to read the data.

3rd byte: Slave address + Read instruction

4th byte: Data read out from the address specified in the second byte.

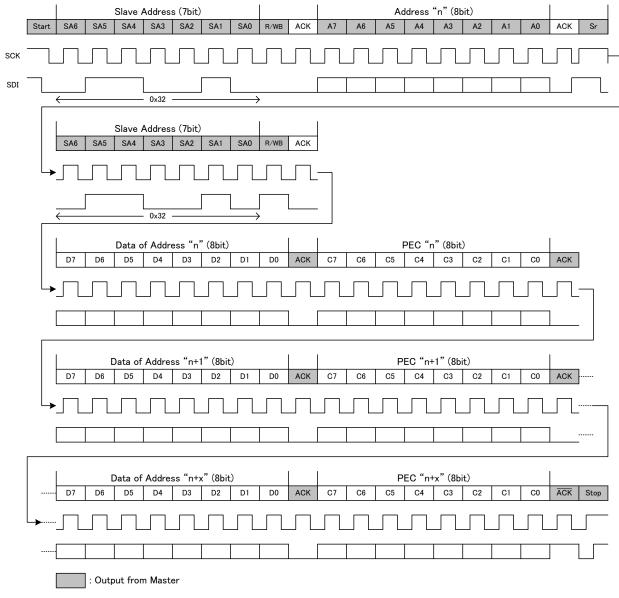
 5^{th} byte: Packet error code (PEC) only when including the CRC data

The PEC is an 8-bit data to indicate the result of the CRC error detection. The CRC is calculated after the second start and uses the slave address and data byte. When burst write transaction, the CRC for subsequent data bytes is calculated over the data byte only.

 $C(x) = X^8 + X^2 + X^1 + 1$

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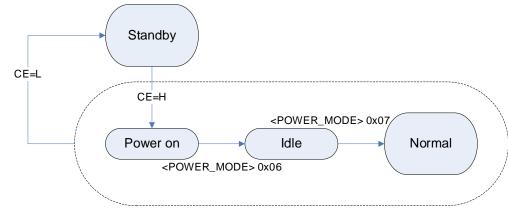
An example of the burst read format is as follows:



Read Timing Chart (with CRC, Continuous reading)

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Power on Sequence

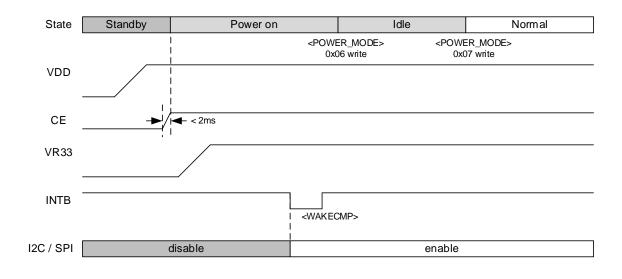


Power Mode Transition Diagram

The 5602L enters in Standby state by the CE pin being Low when connecting with a battery. Even if having connected with the battery, the R5602L enters in Standby state by the CE pin being Low. The Standby state goes to the Normal state by the CE pin being High.

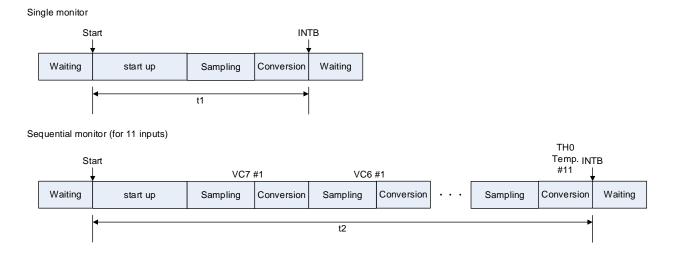
In the Normal state, setting the register enables a sequential reading for voltage, current, and temperature. In addition, the Cell Balancing, and the open-wire detection registers can be set individually.

The sequence is shown below.



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Single and Sequential Read Status



Monitoring Timing Diagram

The ADC monitors in fixed order as shown in above timing charts. The sequential read setting is possible to skip monitoring unassigned VCn pins. The start-up time is 60us, the conversion time is 30µs. t1 and t2 are is specified by the sampling time set registers and the averaged read time set registers.

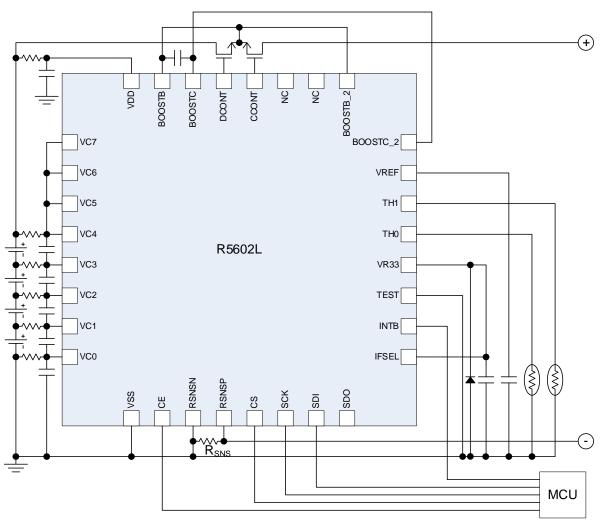
Minimum sampling time settings are 80µs for VCn at 3 V ≤ V_{VCIN} ≤ 4.5 V, 400µs for VCn at 1.5 V ≤ V_{VCIN} < 3 V, 40us for the others, respectively. (n: 1 to 7)

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Battery Connection

The R5602L can support from four- to seven-cell. When using six-cell or less as shown the below diagram, contiguous lower input pins (VC0 to VC4) must be connected with a battery in order of lower voltage, and contiguous upper input pins (VC5 to VC7) must be shorted to VC4 that is a highest potential input pin of used input pins.



4-cell Connection with SPI Interface Diagram⁽¹⁾

 $^{^{(1)}}$ A clamp diode is required for VR33 pin. Recommended VF < 0.4V@100mA

POWER DISSIPATION

QFN0505-32C

PD-QFN0505-32-(85125)-JE-A

The power dissipation of the package is dependent on PCB material, layout, and environmental conditions. The following measurement conditions are based on JEDEC STD. 51.

Measurement Conditions

ltem	Measurement Conditions					
Environment	Mounting on Board (Wind Velocity = 0 m/s)					
Board Material	Glass Cloth Epoxy Plastic (Four-Layer Board)					
Board Dimensions	76.2 mm × 114.3 mm × 1.6 mm					
Copper Ratio	Outer Layer (First Layer): Less than 10% Inner Layers (Second and Third Layers): Approx. 100% of 74.2 mm Square Outer Layer (Fourth Layer): Less than 10%					
Through-holes	φ 0.3 mm × 9pcs					

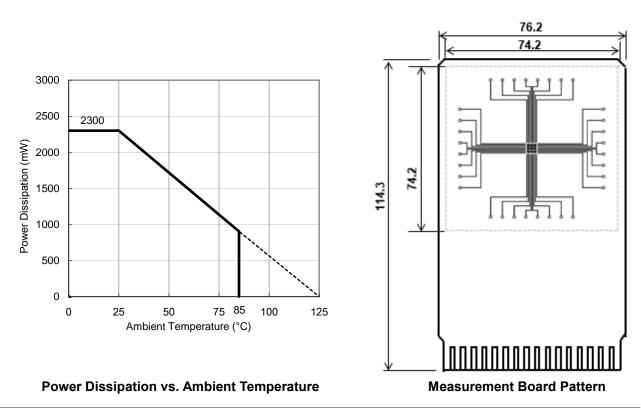
Measurement Result

(Ta = 25°C, Tjmax = 125°C)

Item	Measurement Result
Power Dissipation	2300mW
Thermal Resistance (θja)	θja = 43°C/W
Thermal Characterization Parameter (ψjt)	ψjt = 16°C/W

 θ ja: Junction-to-Ambient Thermal Resistance

wit: Junction-to-top of package thermal characterization parameter

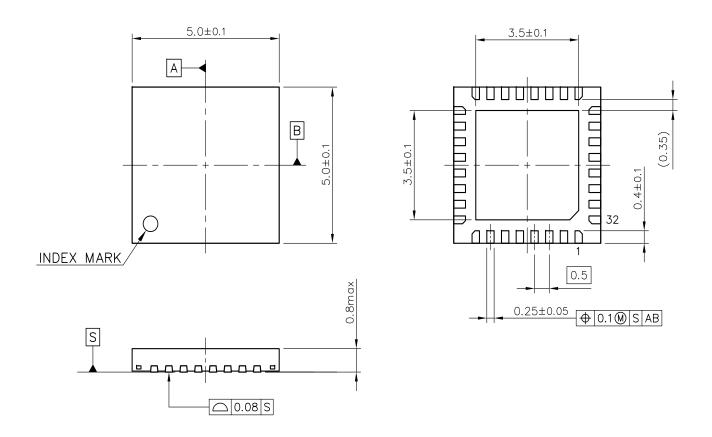


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PACKAGE DIMENSIONS

QFN0505-32C

DM-QFN0505-32C-JE-A



QFN0505-32C Package Dimensions (Unit: mm)

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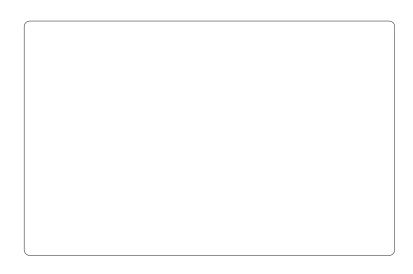
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